WHAT IS CLAIMED IS:

1. A method of manufacturing an electro-optical device, the electro-optical device having an electro-optical element formed by laminating at least a first electrode, an electro-optical layer, and a second electrode in sequence on a substrate, comprising:

forming an ultraviolet absorbing layer on the substrate by a vapor deposition method so as to cover the electro-optical element; and

forming a gas barrier layer by a vapor deposition method using a plasma so as to cover the ultraviolet absorbing layer.

2. A method of manufacturing an electro-optical device, comprising :

forming a plurality of first electrodes on a substrate;

forming, on the substrate, a bank structure having a plurality of apertures corresponding to positions at which the first electrodes are formed;

forming electro-optical layers in each of the apertures in the bank structure;

forming a second electrode so as to cover the bank structure and each of the electro-optical layers;

forming an ultraviolet absorbing layer on the substrate by a vapor deposition method so as to cover the second electrode; and

forming a gas barrier layer by a vapor deposition method usingplasma so as to cover the ultraviolet absorbing layer.

3. The method according to claim 2,

an angle of a face constituting an outer side of the bank structure with respect to a surface of the substrate being 110° or more.

4. The method according to claim 1,

the gas barrier layer being formed by a high-density plasma under reduced pressure.

5. The method according to claim 1,

the ultraviolet absorbing layer including an oxide semiconductor material having an energy band gap of 2 eV to 6 eV, as a primary component.

6. The method according to claim 5,

the ultraviolet absorbing layer including an oxide semiconductor material having an energy band gap of 3 eV to 6 eV, as a primary component.

7. The method according to any one of claim 1,

the ultraviolet absorbing layer having photocatalyst activity by the ultraviolet light generated from the plasma used in the forming of the gas barrier layer.

8. The method according to claim 7,

the ultraviolet absorbing layer including as a primary component, a n-type light-transmitting oxide semiconductor material containing any one of titanium, zinc, and tin.

9. The method according to claim 7,

the ultraviolet absorbing layer containing at least one element of platinum, gold, silver, and copper.

10. The method according to claim 7,

the ultraviolet absorbing layer formed on an exposed surface of the second electrode.

11. The method according to claim 10,

nitrogen being contained in at least a face of the ultraviolet absorbing layer contiguous with the second electrode.

12. The method according to claim 10,

at least a face of the second electrode contiguous with the ultraviolet absorbing layer formed of an inorganic oxide.

13. The method according to claim 10,

from the forming of the second electrode to the forming of the gas barrier layer being continuously performed under reduced pressure by a vapor deposition method.

14. The method according to claim 1, further comprising:

forming a buffer layer to planarize an underlying uneven shape between the second electrode and the ultraviolet absorbing layer.

15. The method according to claim 14,

the buffer layer formed of an organic material.

16. The method according to claim 14,

the buffer layer formed by a liquid phase method.

17. The method according to claim 16, further comprising:

forming an electrode protecting layer to protect the second electrode between the second electrode and the buffer layer.

18. The method according to claim 17,

the electrode protecting layer composed of a silicon compound.

19. The method according to claim 14, further comprising:

forming a buffer layer protecting layer between the buffer layer and the ultraviolet absorbing layer.

20. The method according to claim 19,

the buffer layer protecting layer being composed of an insulating material.

21. The method according to claim 1,

the gas barrier layer formed of a silicon compound.

22. The method according to claim 21,

nitrogen contained in the gas barrier layer.

23. The method according to claim 1,

a laminated film of the ultraviolet absorbing layer and the gas barrier layer having a layer thickness of 500 nm or less.

24. An electro-optical device, comprising:

a first electrode:

an electro-optical layer;

a second electrode;

an ultraviolet absorbing layer, and

a gas barrier layer, each layer being laminated in sequence on a substrate.

25. The electro-optical device according to claim 24,

a protecting layer is provided on the gas barrier layer.

26. The electro-optical device according to claim 25,

a surface protecting layer provided on the protecting layer.

27. An electronic apparatus, comprising:

the electro-optical device according to claim 24.